



VOIDLESS HERMETICALLY SEALED SWITCHING DIODES

Qualified per MIL-PRF-19500/578

Qualified Levels:
JAN, JANTX,
JANTXV and JANS

DESCRIPTION

This popular surface mount equivalent JEDEC registered switching/signal diodes are military qualified and available with internal metallurgical bonded construction. These small low capacitance diodes with very fast switching speeds are hermetically sealed and bonded into a "D-5D" package. They may be used in a variety of fast switching applications including computers and peripheral equipment such as magnetic cores, thin-film memories, plated-wire memories, as well as decoding or encoding applications, etc. Microsemi also offers a variety of other switching/signal diodes.

Important: For the latest information, visit our website <http://www.microsemi.com>.



"D" SQ-MELF (D-5D) Package

Also available in:

"D" Package

(axial-leaded)

 [1N6638 42 43](#)

FEATURES

- JEDEC registered surface mount equivalents of 1N6638, 1N6642, and 1N6643.
- Ultra fast recovery time.
- Very low capacitance.
- Metallurgically bonded.
- Non-cavity glass package.
- JAN, JANTX, JANTXV and JANS qualifications are available per MIL-PRF-19500/578.
- Replacements for 1N4148UR, 1N4148UR-1, 1N4150UR-1, and 1N914UR.
- RoHS compliant devices available (commercial grade only).

APPLICATIONS / BENEFITS

- Small size for high density mounting (see package illustration).
- Ideal for:
 - High frequency data lines
 - RS-232 & RS-422 Interface Networks
 - Ethernet: 10 Base T
 - Switching core drivers
 - LAN
 - Computers

MAXIMUM RATINGS @ T_A = +25 °C unless otherwise noted.

Parameters/Test Conditions	Symbol	Value	Unit
Junction and Storage Temp	T _J and T _{STG}	-65 to +175	°C
Thermal Resistance Junction-to-End Cap	R _{θJEC}	40	°C/W
Thermal Resistance Junction-to-Ambient ⁽¹⁾	R _{θJA}	250	°C/W
Peak Forward Surge Current @ T _A = +25 °C (Test pulse = 8.3 ms, half-sine wave.)	I _{FSM}	2.5	A
Average Rectified Forward Current @ T _A = +75 °C (Derate at 4.6 mA/°C Above T _{EC} = + 110 °C)	I _O	300	mA
Breakdown Voltage:	V _{BR}	150 100 75	V
Working Peak Reverse Voltage:	V _{RWM}	125 75 50	V

NOTES: 1. T_A = +75 °C on printed circuit board (PCB), PCB = FR4 - .0625 inch (1.59 mm) 1-layer 1-Oz Cu, horizontal, in still air; pads for US = .061 inch (1.55 mm) x .105 inch (2.67 mm); R_{θJA} with a defined PCB thermal resistance condition included, is measured at I_O = 300 mA.

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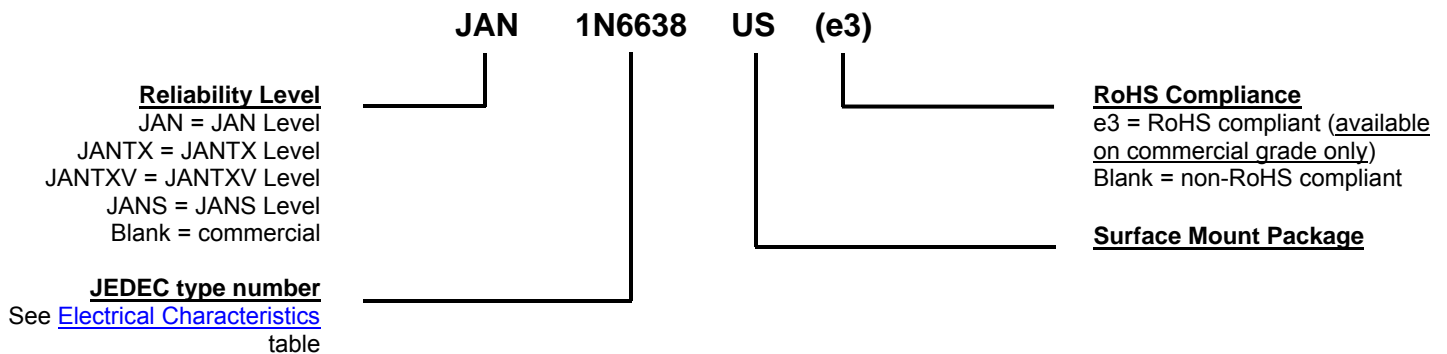
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MECHANICAL and PACKAGING

- CASE: Voidless hermetically sealed hard glass.
- TERMINALS: Tin-Lead plate with >3% Lead. Solder dip is available upon request.
- MARKING: Body painted and alpha numeric.
- POLARITY: Cathode indicated by band.
- Tape & Reel option: Standard per EIA-481-1-A with 12 mm tape. Consult factory for quantities.
- See [Package Dimensions](#) on last page.

PART NOMENCLATURE

SYMBOLS & DEFINITIONS

Symbol	Definition
V_{BR}	Minimum Breakdown Voltage: The minimum voltage the device will exhibit at a specified current.
V_{RWM}	Working Peak Reverse Voltage: The maximum peak voltage that can be applied over the operating temperature range.
V_F	Maximum Forward Voltage: The maximum forward voltage the device will exhibit at a specified current.
I_R	Maximum Reverse Current: The maximum reverse (leakage) current that will flow at the specified voltage and temperature.
C	Capacitance: The capacitance in pF at a frequency of 1 MHz and specified voltage.
t_{rr}	Reverse Recovery Time: The time interval between the instant the current passes through zero when changing from the forward direction to the reverse direction and a specified recovery decay point after a peak reverse current is reached.

ELECTRICAL CHARACTERISTICS @ 25°C unless otherwise noted.

TYPE NUMBER	MAXIMUM FORWARD VOLTAGE $V_F @ I_F$		MAXIMUM DC REVERSE CURRENT				REVERSE RECOVERY TIME t_{rr} (Note 1)	MAXIMUM FORWARD RECOVERY VOLTAGE AND TIME $I_F=200mA, t_r=1ns$		MAXIMUM JUNCTION CAPACITANCE $f = 1 MHz$ $V_{sig} = 50 mV$ (p-p)	
			I_{R1}	I_{R2}	I_{R3}	I_{R4}		V_{FRM}	t_{fr}	$V_R=0 V$	$V_R=1.5 V$
			$V_R=20 V$	$V_R=V_{RWM}$	$V_R=20 V$ $T_A=+150 ^\circ C$	$V_R=V_{RWM}$ $T_A=+150 ^\circ C$					
	V @ mA	V @ mA	nA	nA	μA	μA	ns	V	ns	pf	pf
1N6638US	0.8 V @ 10 mA	1.1 V @ 200 mA	35	500	50	100	4.5	5.0	20	2.5	2.0
1N6642US	0.8 V @ 10 mA	1.2 V @ 100 mA	25	500	50	100	5.0	5.0	20	5.0	2.8
1N6643US	0.8 V @ 10 mA	1.2 V @ 100 mA	50	500	75	100	6.0	5.0	20	5.0	2.8

NOTE: 1. Reverse Recovery Time Test Conditions – $I_F=I_R=10 mA$, $I_{R(REC)} = 1.0 mA$, $C=3 pF$, $R_L = 100 ohms$.

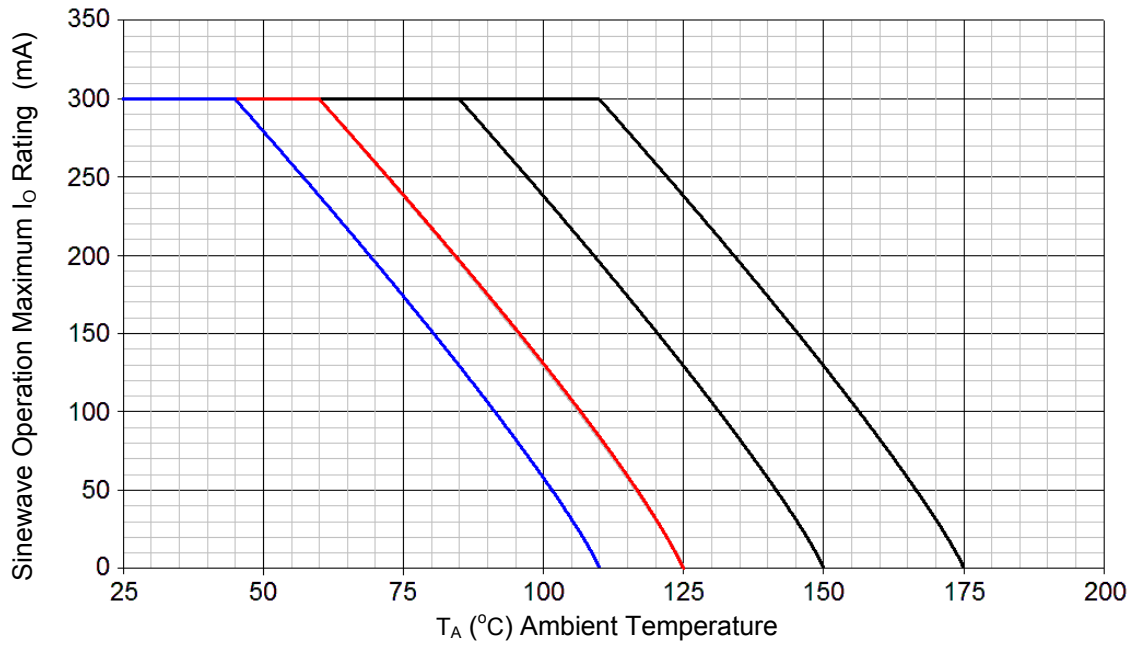
GRAPHS


FIGURE 1
Temperature - Current Derating

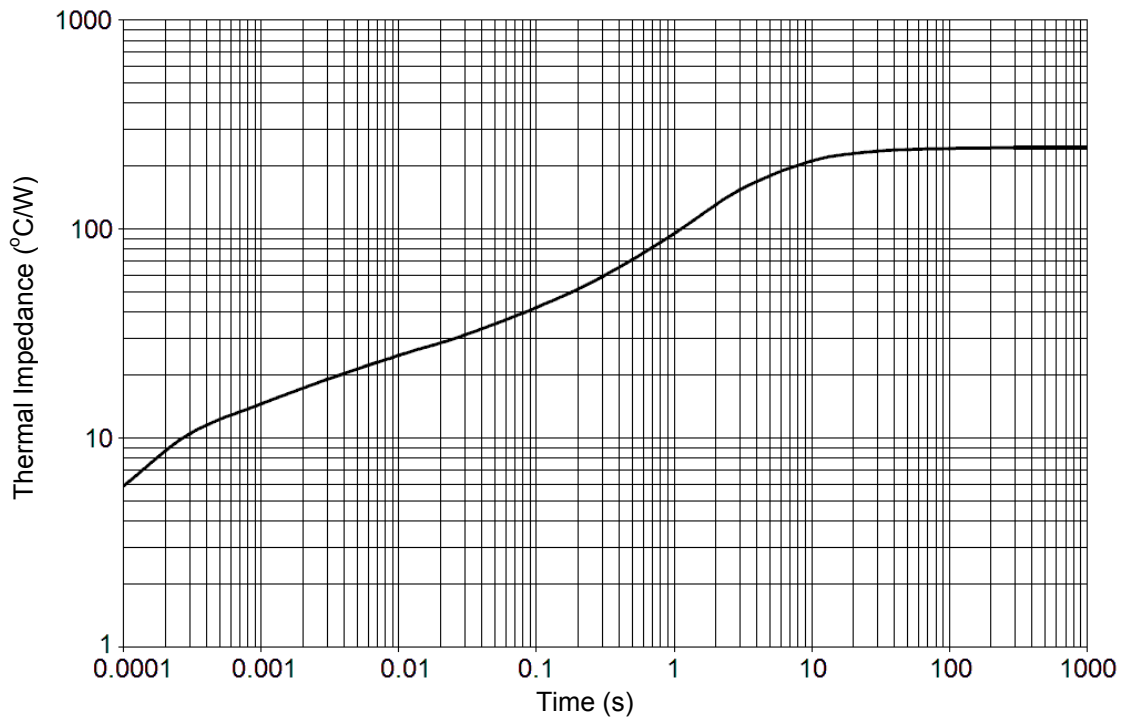


FIGURE 2
Maximum Thermal Impedance at $T_A = 55\text{ °C}$

GRAPHS (continued)



FIGURE 3
Maximum Thermal Impedance at $T_{EC} = 25\text{ }^{\circ}\text{C}$